

Appl. No. 10/632,752

Amdt. dated 4/22/05

Reply to Office action of March 29, 2005

oxide layer forms in air, said material of said capping layer being doped ~~with a doping~~ and said oxide layer including a region having a layer thickness with the same doping as ~~said doping of said capping layer~~, said same doping being incorporated into an oxide of said oxide layer.

Claim 12 (original). The reflective mirror according to claim 11, wherein said layer thickness of said oxide layer is between 0.8 and 2.0 nm.

Claim 13 (original). The reflective mirror according to claim 11, wherein said capping layer is formed of n-doped silicon..

Claim 14 (original). The reflective mirror according to claim 11, wherein said capping layer is doped with a material selected from the group consisting of phosphorus and arsenic.

Claim 15 (original). The reflective mirror according to claim 11, wherein said capping layer is amorphous.

Claim 16 (original). The reflective mirror according to claim ¹¹~~2~~, which further comprises a patterned mask layer for patterning a semiconductor product.

ABR(12/23/05)